NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **MRAL2023-3** is a Common Base Device Designed for class C Amplifier Applications in L-Band FM Microwave Links.

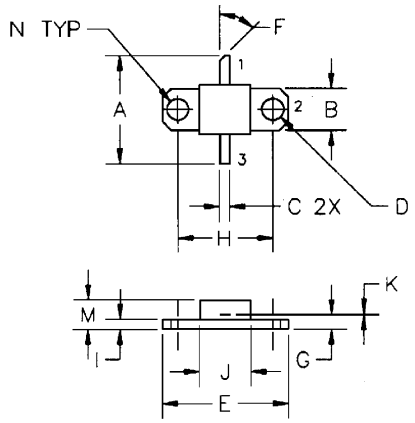
FEATURES INCLUDE:

- Gold Metallization
- Emitter Ballasting
- Input Matching

MAXIMUM RATINGS

I_C	0.5 A
V_{CES}	40 V
P_{DISS}	10 W @ T_C = 25 ^{O}C
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +150 ^{O}C
θ_{JC}	16 ^{O}C/W

PACKAGE STYLE .250 2L FLG (C)



1 = COLLECTOR 2 = BASE
3 = EMITTER

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I_C = 20 mA	40			V
BV_{EBO}	I_E = 1.0 mA	3.5			V
I_{CBO}	V_{CB} = 22 V			1.0	mA
h_{FE}	V_{CE} = 5.0 V I_C = 200 mA	10			---
C_{OB}	V_{CB} = 22 V f = 1.0 MHz			5	pF
P_G η_C	V_{CE} = 22 V P_{OUT} = 3.0 W f = 2000 to 2300 MHz	8.0	8.5 45		dB %

ADVANCED SEMICONDUCTOR, INC.
7525 ETHEL AVENUE • NORTH HOLLYWOOD, CA 91605 • (818) 982-1200 • FAX (818) 765-3004

Specifications are subject to change without notice.